Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	50877	((cvd (chemical same vapor same deposit$3) ALD (atomic same layer same deposit$3) pulse plasma)).CLM.	US-PGPUB	OR	ON	2005/12/05 11:36
L2	679	((substrate wafer) and (reactor chamber) and (vapor and (reactant precursor))).CLM.	US-PGPUB	OR	ON	2005/12/05 11:37
L4	48092	(pulse cycle).CLM.	US-PGPUB	OR	ON	2005/12/05 11:37
L10	30418	(PSG (phosphosilicate and glass) (phosphorous and dop$3 (("Si" "O.sub.2"))) (silicon same (oxide dioxide))).CLM.	US-PGPUB	OR	ON	2005/12/05 11:38
L12	50964	((cvd chemisorb$3 (chemical same vapor same deposit$3) ALD (atomic same layer same deposit$3) pulse plasma)). CLM.	US-PGPUB	OR	ON	2005/12/05 11:40
L13	50964	L1 L12	US-PGPUB	OR	ON	2005/12/05 11:40
L14	49	L2 and L4 and L10	US-PGPUB	OR	ON	2005/12/05 11:40

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	36581	ALD (atomic near5 layer near5 deposit$3)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:09
L3	56	L2 and (phosphorus near5 (silicon near5 (oxide dioxide)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:09
L4	56	L3 and phosphorus	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:09
L5	14192	PSG (phosphours near5 doped near5 (silicon near5 (dioxide oxide)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:11
L6	14192	PSG (phosphours near5 dop$3 near5 (silicon near5 (dioxide oxide)))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:11
L7	14192	L5 L6	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:11
L8	372	L7 and (ALD (atomic near5 layer near5 deposit$3))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:11
L9	3012	pulse near5 deposit$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:12
L10	565	L9 and (silicon near5 oxide)	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:12
L11	87	("Si" near5 "O" near5 "CH" near5 "OH")	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:12
L15	3379	chemisorb$3	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:15
L16	3047	L15 and (silicon (oxide dioxide))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:15
L17	548	L16 and phosphorus	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:15

L18	248	L17 and (pulse cvd ALD (atomic near5 layer near5 deposit$3) plasma (chemical near5 vapor near5 deposit$3))	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/05 11:15
L19	431	chemisorb$3	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 11:17
L20	137	L19 and (silicon (oxide dioxide))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 11:17
L21	3	L20 and phosphorus	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 11:17
L22	240390	(plasma cvd ALD (atomic near5 layer near5 deposit$3) (chemical near5 vapor near5 deposit$3))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 11:18
L23	2081	L22 and (BPSG PSG (borophosphosilicate near5 glass) (dop$3 near5 silicon near5 (oxide dioxide)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 11:18
L24	38	L23 and (phosphorus near5 dop$3 near5 silicon near5 (oxide dioxide))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/05 11:18